2SA673(A)

Rev.E Mar.-2016

描述 / Descriptions

TO-92 塑封封装 PNP 半导体三极管。Silicon PNP transistor in a TO-92 Plastic Package.

特征 / Features

与 2SC1213(A)互补。

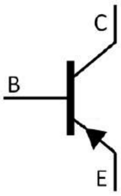
Complementary pair with 2SC1213(A).

用途 / Applications

用于低频放大。

Low frequency power amplifier.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning

PIN1：Base　　PIN 2：Collector　　PIN 3：Emitter

放大及印章代码 / hFE Classifications & Marking

h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	60~120	100~200	160~320

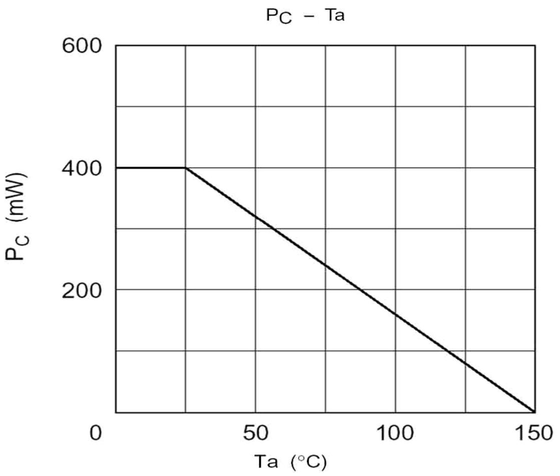
极限参数 / Absolute Maximum Ratings(Ta=25℃)

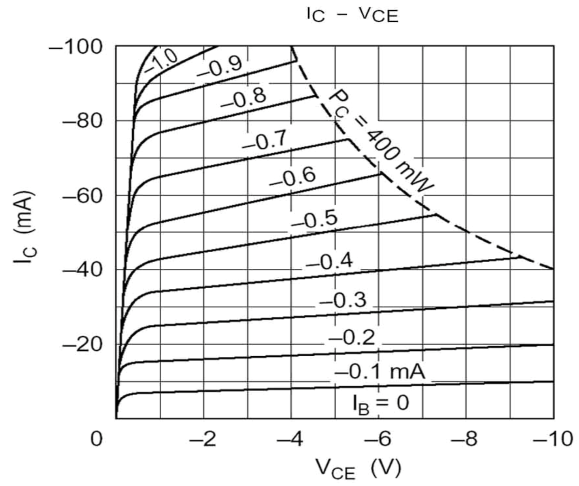
参数 Parameter	符号 Symbol		数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	2SA673	-35	V
		2SA673A	-50	
Collector to Emitter Voltage	V_{CEO}	2SA673	-35	V
		2SA673A	-50	
Emitter to Base Voltage	V_{EBO}		-4.0	V
Collector Current - Continuous	I_C		-500	mA
Collector Power Dissipation	P_C		400	mW
Junction Temperature	T_j		150	℃
Storage Temperature Range	T_{stg}		-55～150	℃

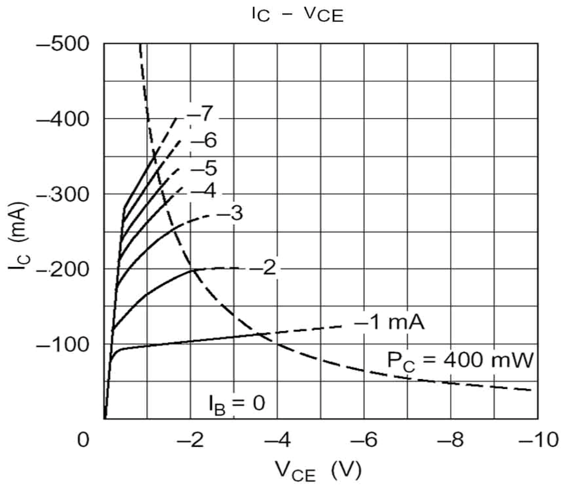
电性能参数 / Electrical Characteristics(Ta=25℃)

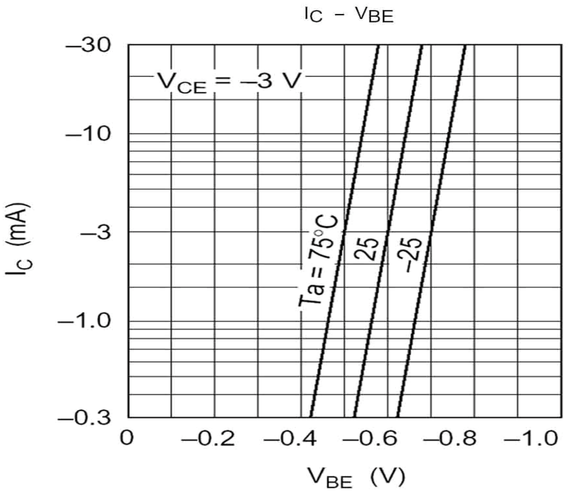
参数 Parameter	符号 Symbol		测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	V_{CBO}	2SA673	I_C=-10μA I_E=0	-35			V
		2SA673A		-50			
Collector to Emitter Breakdown Voltage	V_{CEO}	2SA673	I_C=-1.0mA I_B=0	-35			V
		2SA673A		-50			
Emitter to Base Breakdown Voltage	V_{EBO}		I_E=-10μA I_C=0	-4.0			V
Collector Cut-Off Current	I_{CBO}		V_{CB}=-20V I_E=0			-0.5	μA
DC Current Gain	$h_{FE(1)}$		V_{CE}=-3.0V I_C=-10mA	60		320	
	$h_{FE(2)}$		V_{CE}=-3.0V I_C=-500mA	10			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$		I_C=-150mA I_B=-15mA		-0.2	-0.6	V
Base to Emitter Voltage	V_{BE}		V_{CE}=-3.0V I_C=-10mA		-0.64		V

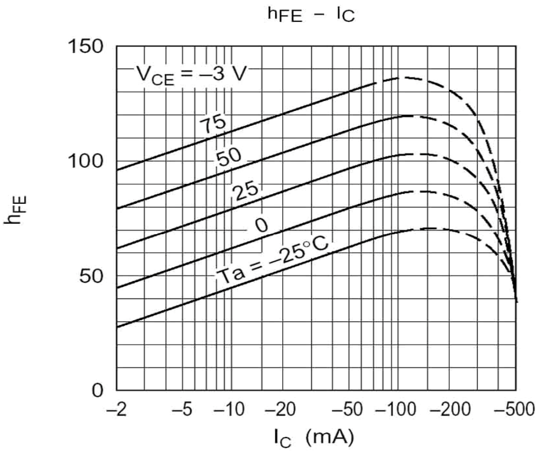
电参数曲线图 / Electrical Characteristic Curve

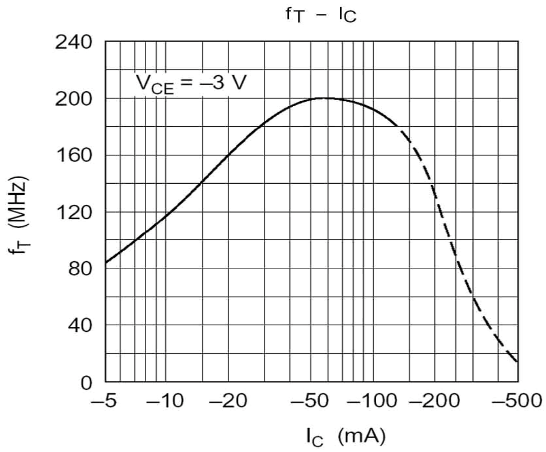






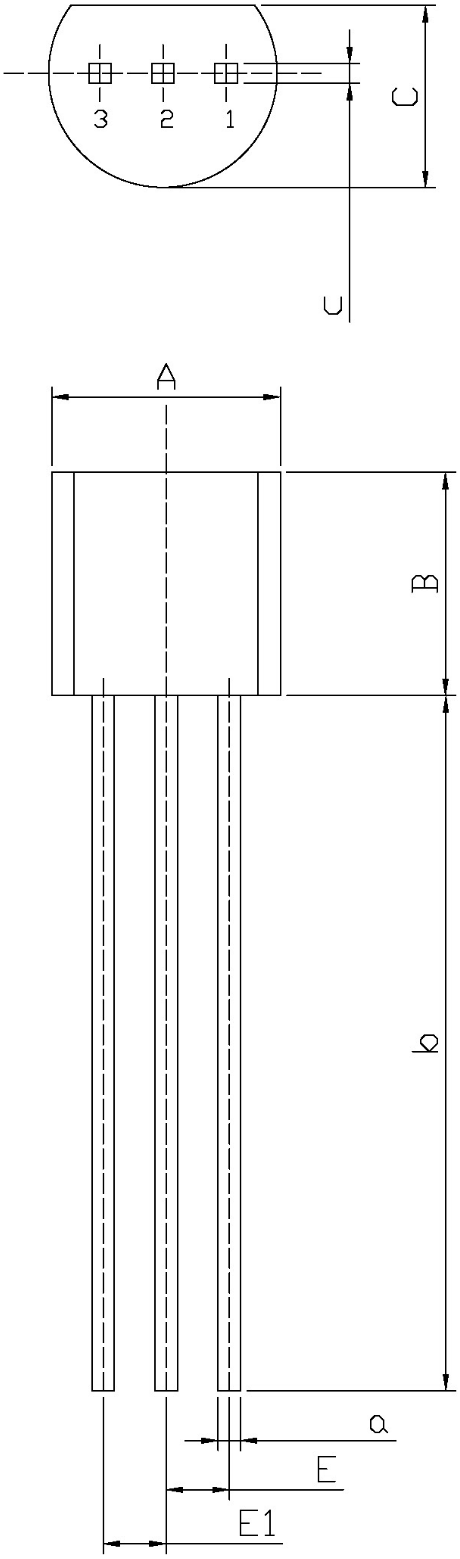






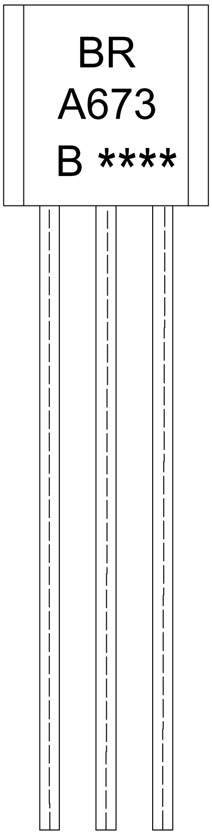
外形尺寸图 / Package Dimensions

TO-92 Unit: mm



Symbol	Dimensions In Millmeters	
	Min	Max
A	4.4	4.8
B	4.3	4.7
b	13	15
a	0.40	0.60
E	1.22	1.32
E1	1.22	1.32
C	3.4	3.8
c	0.30	0.50

印章说明 / Marking Instructions



说明：

BR: 为公司代码

A673： 为型号代码

B: 为 h_{FE} 分档代码

****： 为生产批号代码，随生产批号变化。

Note:

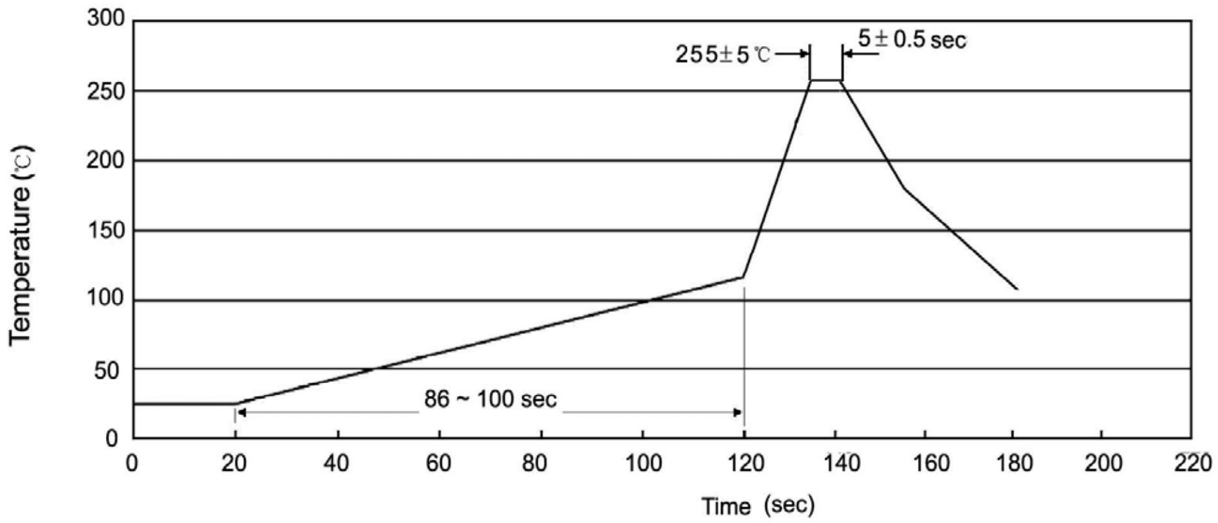
BR: Company Code.

A673: Product Type.

B: h_{FE} Classifications Symbol

****: Lot No. Code,code change with Lot No.

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明：
1、预热温度 25 ~ 150℃，时间 60 ~ 90sec;
2、峰值温度 255±5℃，时间持续为 5±0.5sec;
3、焊接制程冷却速度为 2 ~ 10℃/sec.

Note:
1.Preheating:25~150℃, Time:60~90sec.
2.Peak Temp.:255±5℃, Duration:5±0.5sec.
3. Cooling Speed: 2~10℃/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5℃　　时间：10±1 sec.

Temp:270±5℃　　Time:10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

编带包装 / AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	Units/tape 只/纸带	Tape/Inner Box 纸带/盒	Rows/Inner Box 纸带层/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Inner Box 盒	Outer Box 箱
TO-92	3,000	1	120	10	30,000	328×230×42	小箱 480×346×235, 大箱 547×407×268

使用说明 / Notices